**Preferred Device** 

# Triacs

## **Silicon Bidirectional Thyristors**

Designed primarily for full wave ac control applications, such as motor controls, heating controls or dimmers; or wherever full–wave, silicon gate–controlled devices are needed.

#### Features

- High Commutating di/dt and High Immunity to dV/dt @ 125°C
- Minimizes Snubber Networks for Protection
- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS
- High Surge Current Capability 150 Amperes
- Industry Standard TO-220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity
- Operational in Three Quadrants, Q1, Q2, and Q3
- Pb–Free Packages are Available\*

#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

Rating	Symbol	Value	Unit
$\begin{array}{l} \mbox{Peak Repetitive Off-State Voltage (Note 1)} \\ (T_J = -40 \mbox{ to } 125^\circ\mbox{C}) & MAC16\mbox{CM} \\ MAC16\mbox{CN} \end{array}$	V <sub>DRM,</sub> V <sub>RRM</sub>	600 800	V
On-State RMS Current (Full Cycle Sine Wave 50 to 60 Hz; $T_{C} = 80^{\circ}C$ )	I <sub>T(RMS)</sub>	16	A
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T <sub>J</sub> = 125°C)	I <sub>TSM</sub>	150	A
Circuit Fusing Consideration (t = 8.33 ms)	l <sup>2</sup> t	93	A <sup>2</sup> sec
Peak Gate Power (Pulse Width $\leq$ 1.0 $\mu$ s, T <sub>C</sub> = 80°C)	P <sub>GM</sub>	20	W
Average Gate Power (t = 8.3 ms, $T_C = 80^{\circ}C$ )	P <sub>G(AV)</sub>	0.5	W
Operating Junction Temperature Range	Τ <sub>J</sub>	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

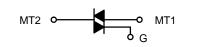
 V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

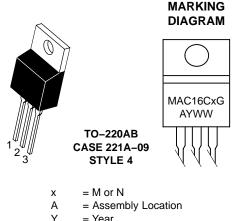


### **ON Semiconductor®**

http://onsemi.com

## TRIACS 16 AMPERES RMS 400 thru 800 VOLTS





= Year

WW = Work Week

G = Pb–Free Package

	PIN ASSIGNMENT
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

#### ORDERING INFORMATION

Device	Package	Shipping
MAC16CM	TO-220AB	50 Units / Rail
MAC16CMG	TO-220AB (Pb-Free)	50 Units / Rail
MAC16CN	TO-220AB	50 Units / Rail
MAC16CNG	TO-220AB (Pb-Free)	50 Units / Rail

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient	$R_{ extsf{ heta}JC}$ $R_{ hetaJA}$	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	ΤL	260	°C

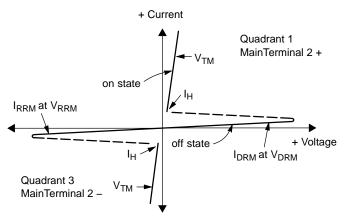
### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

Characteristic		nbol Mi	n Ty	γp	Max	Unit
OFF CHARACTERISTICS	•			1		
		RM, RM –	-	-	0.01 2.0	mA
ON CHARACTERISTICS	·					
Peak On-State Voltage (Note 2) ( $I_{TM} = \pm 21 \text{ A Peak}$ )	V	тм –	1.	2	1.6	V
Gate Trigger Current (Continuous DC) $(V_D = 12 V, R_L = 100 \Omega)$ MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	I.	GT 8. 8. 8.	0 1	-	35 35 35	mA
Holding Current ( $V_D = 12 V$ , Gate Open, Initiating Current = $\pm 150 \text{ mA}$ )		Чн –	2	0	50	mA
Latching Current (V <sub>D</sub> = 12 V, I <sub>G</sub> = 35 mA) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		IL – –	2 4 2	0	50 80 50	mA
Gate Trigger Voltage (Continuous DC) $(V_D = 12 \text{ V}, \text{R}_L = 100 \Omega)$ MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	V	GT 0 0 0	5 0.	72	1.5 1.5 1.5	V
DYNAMIC CHARACTERISTICS			ľ			
Rate of Change of Commutating Current ( $V_D = 400 \text{ V}, I_{TM} = 6.0 \text{ A}, \text{ Commutating dV/dt} = 24 \text{ V/}\mu\text{s}, \text{ Gate Open}, $ $T_J = 125^{\circ}\text{C}, f = 250 \text{ Hz}, C_L = 10 \mu\text{F}, L_L = 40 \text{ mH}, \text{ with Snubber})$	(di.	/dt) <sub>c</sub> 15	5 -	-	-	A/ms
Critical Rate of Rise of Off-State Voltage $(V_D = Rated V_{DRM}, Exponential Waveform,$ Gate Open, $T_J = 125^{\circ}C$ )	d\	//dt 60	0 -	-	-	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 μsec; diG/dt = 200 mA/μsec; f = 60 Hz	d	i/dt –	-	-	10	A/μs

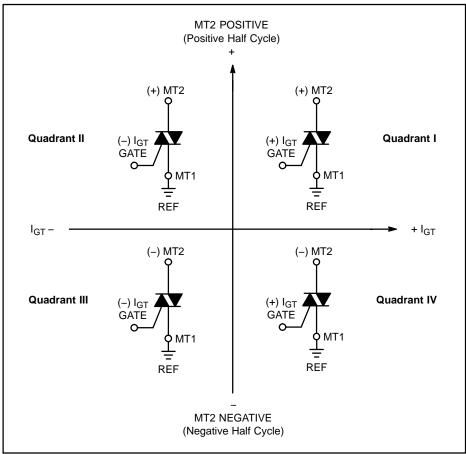
2. Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%.

#### Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current

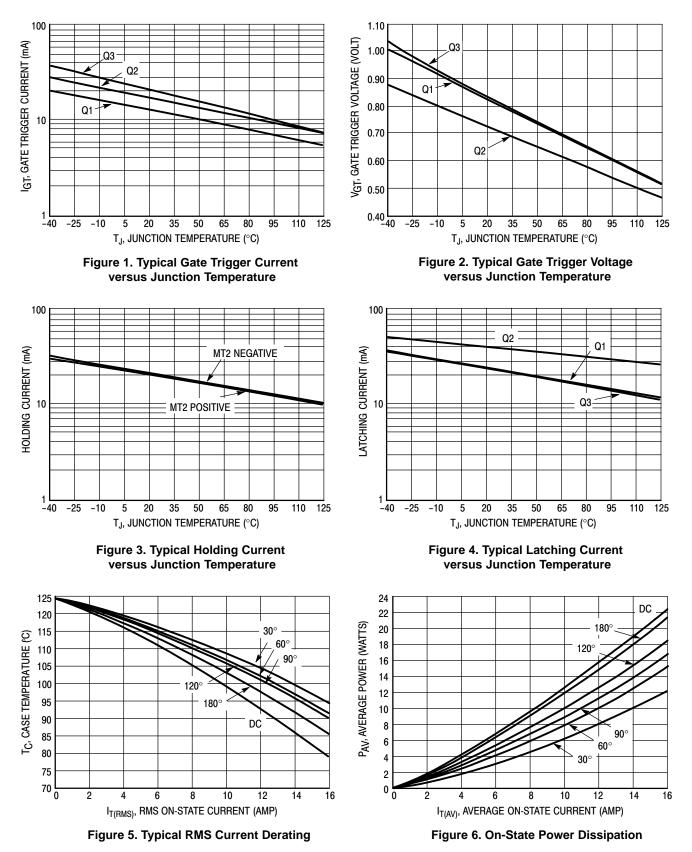


#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



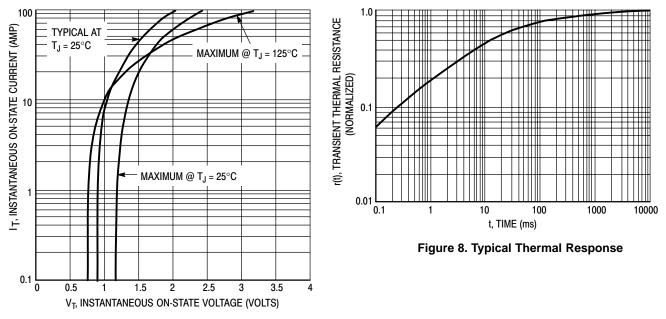
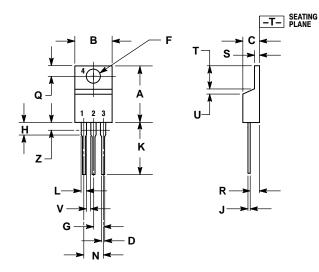


Figure 7. On-State Characteristics

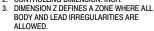
#### PACKAGE DIMENSIONS

**TO-220AB** CASE 221A-09 **ISSUE AA** 



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.

2



	INCHES MILLIMETE			IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
Κ	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
Ν	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
۷	0.045		1.15	
Ζ		0.080		2.04

PIN 1. MAIN TERMINAL 1 2. MAIN TERMINAL 2 3. GATE 4 MAIN TERMINAL 2

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